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(71)Applicant : FUJI ELECTRIC CO LTD

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(72)Inventor : UENO KATSUNORI

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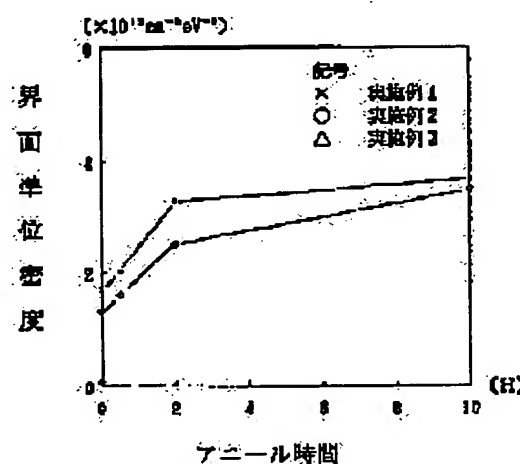
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(54) MANUFACTURE OF SILICON CARBIDE SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To reduce the interface level density after formation of a thermal oxide film of a silicon carbide semiconductor device.

SOLUTION: The anneal time in inert gas after thermal oxidation is made under two hours. Moreover, it will do to heat-treat the thermal oxide film made once in gas including hydrogen atoms such as hydrogen, water, or the like at a low temperature of 300-500°C. Furthermore, after thermal oxidation and in one part at least of the cooling period after heat-treatment process and thermal oxidation, the gas including hydrogen atoms is made atmosphere.



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